

Switch-mode Power Rectifier

MURD320, NRVUD320

DPAK Surface Mount Package

These state-of-the-art devices are designed for use in switching power supplies, inverters and as free wheeling diodes.

Features

- Ultrafast 35 Nanosecond Recovery Time
- Low Forward Voltage Drop
- Low Leakage
- NRVUD, SURD8 Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant*

Mechanical Characteristics

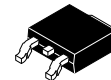
- Case: Epoxy, Molded
- Weight: 0.4 Gram (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Ratings:
 - ♦ Machine Model = C (> 400 V)
 - ♦ Human Body Model = 3B (> 8 kV)

MAXIMUM RATINGS

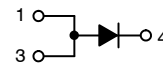
| Rating | Symbol | Value | Unit |
|--|---------------------------------|-------------|------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | V_{RRM} V_{RWM} V_R | 200 | V |
| Average Rectified Forward Current ($T_C = 158^\circ\text{C}$) | $I_{F(AV)}$ | 3.0 | A |
| Peak Repetitive Forward Current (Square Wave, Duty = 0.5, $T_C = 158^\circ\text{C}$) | I_{FRM} | 6.0 | A |
| Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, 60 Hz) | I_{FSM} | 75 | A |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | -65 to +175 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

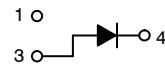
ULTRAFAST RECTIFIER 3.0 AMPERES, 200 VOLTS



DPAK
CASE 369C

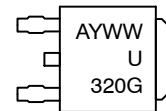


STYLE 3

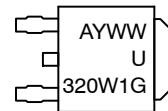


STYLE 8

MARKING DIAGRAM



MURD320T4G
SURD8320T4G
NRVUD320VT4G



NRVUD320W1T4G

A = Assembly Location**
Y = Year
WW = Work Week
G = Pb-Free Package

**The Assembly Location Code (A) is front side optional. In cases where the Assembly Location is stamped in the package bottom (molding ejector pin), the front side assembly code may be blank.

ORDERING INFORMATION

| Device | Package | Shipping† |
|--------------|-------------------|--------------------|
| MURD320T4G | DPAK (Pb-Free) | 2500 / Tape & Reel |
| NRVUD320VT4G | DPAK (Pb-Free) | 2500 / Tape & Reel |

DISCONTINUED (Note 1)

| | | |
|--------------------|-------------------|--------------------|
| NRVUD320W1T4G | DPAK (Pb-Free) | 2500 / Tape & Reel |
| NRVUD320W1T4G-VF01 | DPAK (Pb-Free) | 2500 / Tape & Reel |
| SURD8320T4G | DPAK (Pb-Free) | 2500 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

1. **DISCONTINUED:** This device is not recommended for new design. Please contact your onsemi representative for information. The most current information on this device may be available on www.onsemi.com.

MURD320, NRVUD320

THERMAL CHARACTERISTICS

| Characteristics | Symbol | Value | Unit |
|---|-----------------|-------|---------------|
| Thermal Resistance – Junction-to-Case | $R_{\theta JC}$ | 6 | $^{\circ}C/W$ |
| Thermal Resistance – Junction-to-Ambient (Note 1) | $R_{\theta JA}$ | 80 | $^{\circ}C/W$ |

1. Rating applies when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS

| Characteristics | Symbol | Value | Unit |
|---|----------|--------------|---------|
| Maximum Instantaneous Forward Voltage Drop (Note 2) ($I_F = 3$ Amps, $T_J = 25^{\circ}C$) ($I_F = 3$ Amps, $T_J = 125^{\circ}C$) | V_F | 0.95 0.75 | Volts |
| Maximum Instantaneous Reverse Current (Note 2) ($T_J = 25^{\circ}C$, Rated dc Voltage) ($T_J = 125^{\circ}C$, Rated dc Voltage) | I_R | 5 500 | μA |
| Maximum Reverse Recovery Time ($I_F = 1$ Amp, $di/dt = 50$ Amps/ μs , $V_R = 30$ V, $T_J = 25^{\circ}C$) ($I_F = 0.5$ Amp, $i_R = 1$ Amp, $I_{REC} = 0.25$ A, $V_R = 30$ V, $T_J = 25^{\circ}C$) | t_{rr} | 35 25 | ns |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

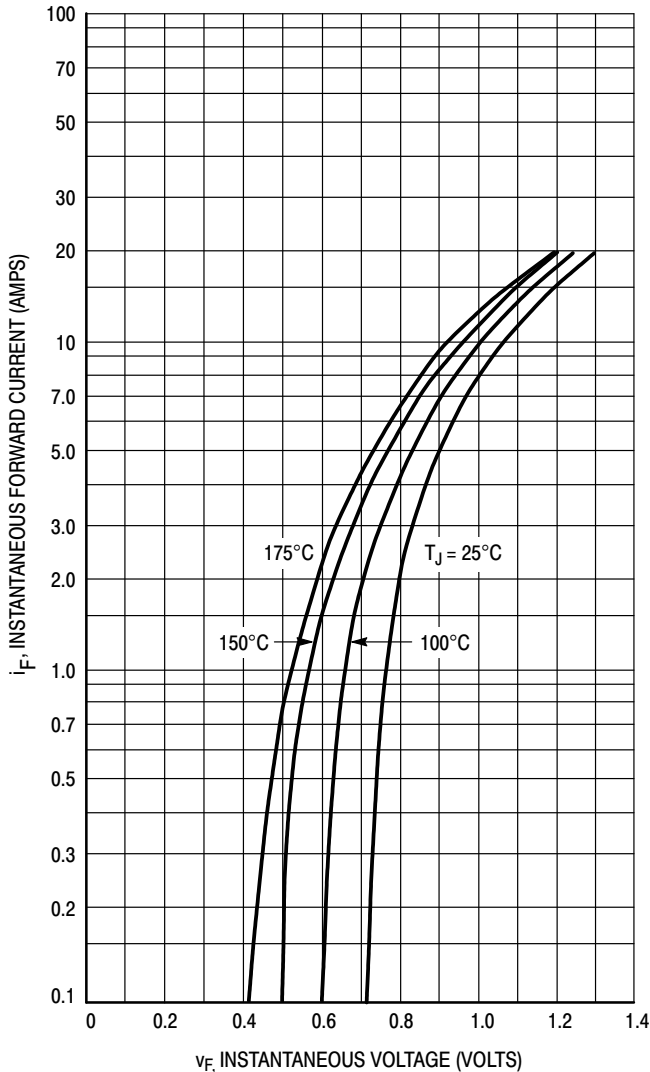


Figure 1. Typical Forward Voltage

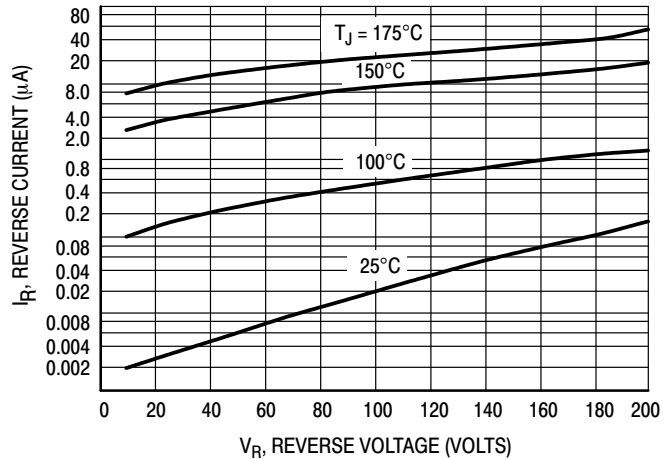


Figure 2. Typical Reverse Current*

* The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these curves if V_R is sufficiently below rated V_R .

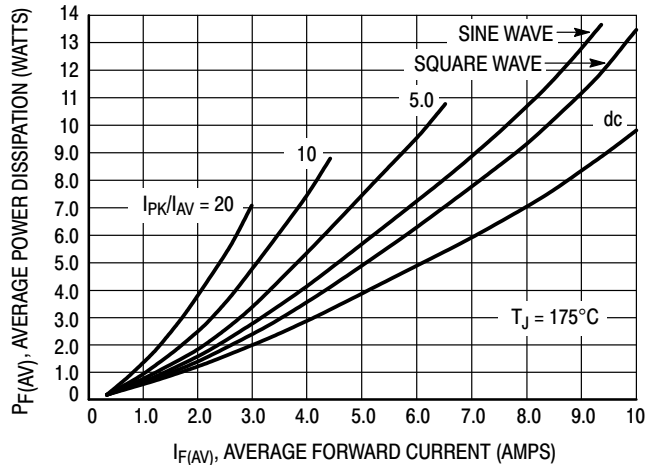


Figure 3. Average Power Dissipation

MURD320, NRVUD320

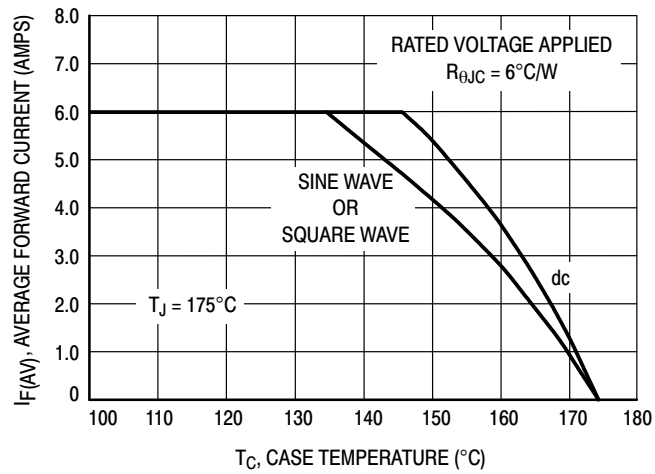


Figure 4. Current Derating, Case

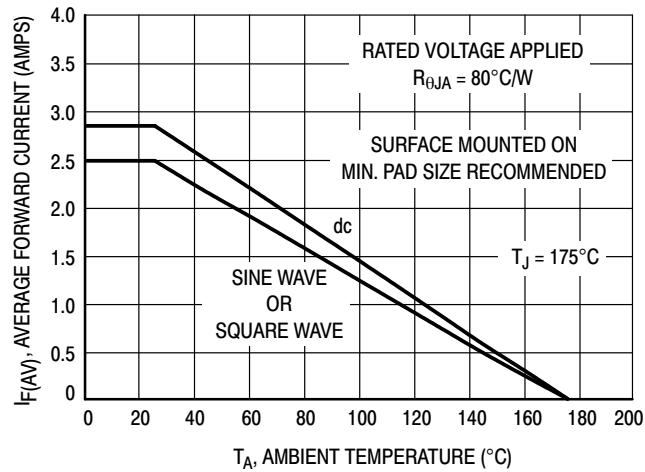


Figure 5. Current Derating, Ambient

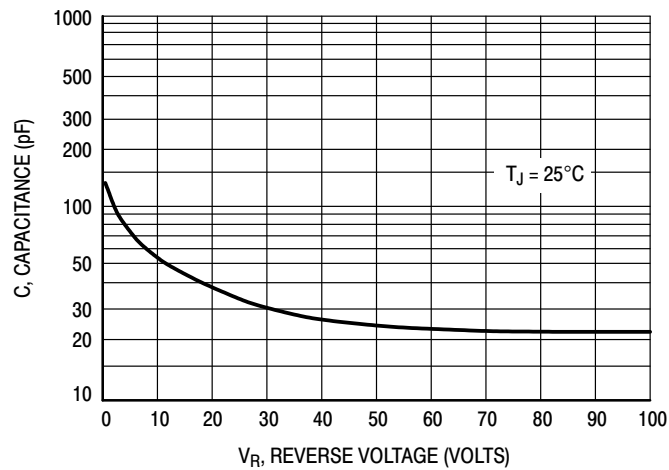
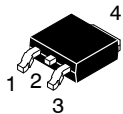


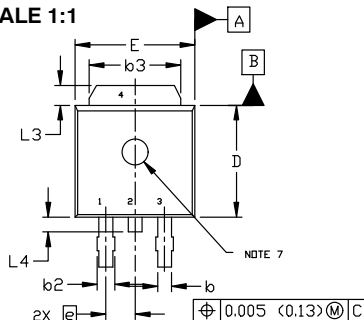
Figure 6. Typical Capacitance



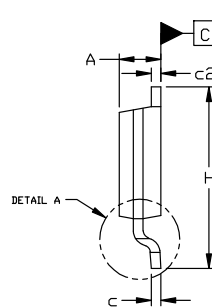
DPAK (SINGLE GAUGE)
CASE 369C
ISSUE G

DATE 31 MAY 2023

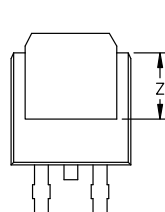
SCALE 1:1



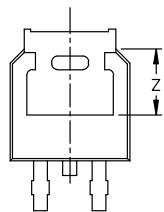
TOP VIEW



SIDE VIEW

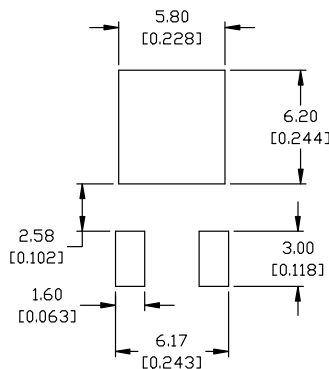


BOTTOM VIEW



BOTTOM VIEW

ALTERNATE
CONSTRUCTIONS



RECOMMENDED MOUNTING FOOTPRINT*

*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLE 1:

PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:

PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:

PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:

PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:

PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:

PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:

PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 8:

PIN 1. N/C
2. CATHODE
3. ANODE
4. CATHODE

STYLE 9:

PIN 1. ANODE
2. CATHODE
3. RESISTOR ADJUST
4. CATHODE

STYLE 10:

PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

NOTES:

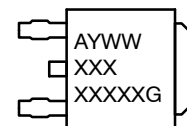
1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 0.086 | 0.094 | 2.18 | 2.38 |
| A1 | 0.000 | 0.005 | 0.00 | 0.13 |
| b | 0.025 | 0.035 | 0.63 | 0.89 |
| b2 | 0.028 | 0.045 | 0.72 | 1.14 |
| b3 | 0.180 | 0.215 | 4.57 | 5.46 |
| c | 0.018 | 0.024 | 0.46 | 0.61 |
| c2 | 0.018 | 0.024 | 0.46 | 0.61 |
| D | 0.235 | 0.245 | 5.97 | 6.22 |
| E | 0.250 | 0.265 | 6.35 | 6.73 |
| e | 0.090 | BSC | 2.29 | BSC |
| H | 0.370 | 0.410 | 9.40 | 10.41 |
| L | 0.055 | 0.070 | 1.40 | 1.78 |
| L1 | 0.114 | REF | 2.90 | REF |
| L2 | 0.020 | BSC | 0.51 | BSC |
| L3 | 0.035 | 0.050 | 0.89 | 1.27 |
| L4 | ---- | 0.040 | --- | 1.01 |
| Z | 0.155 | ---- | 3.93 | --- |

GENERIC
MARKING DIAGRAM*



IC



Discrete

XXXXXX = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

| | | |
|------------------|---------------------|---|
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